

ductor films **840**, **860** results in the creation of an electron and a hole. When the photon is absorbed in the vicinity of the pn junction, the built in electric field separates the two carriers in opposite directions, electrons are driven to the n-type material and holes are driven to the p-type film. The separated charges result in a potential difference between the two semiconductor films **840**, **860**. This potential difference is used to drive a current through an external circuit thereby converting solar energy (photons) into electrical energy.

[0181] One embodiment of a heterojunction, photovoltaic solar cell is an n-type, polycrystalline CdS film as the first semiconductor film **840** and a p-type, polycrystalline CdTe film as the second semiconductor film **860**. CdS has a band gap of 2.43 eV that corresponds to 510 nm. CdTe has a band gap of 1.44 eV that corresponds to 860 nm. Solar radiation shorter than 860 nm and longer than 510 nm is absorbed in the p-type CdTe semiconductor film **860**. Each absorbed photon creates an electron hole pair. If the minority carrier, the electron in p-type CdTe, has a lifetime sufficiently long so that it can drift to the pn junction and be swept across the junction to the n-type CdS film, the absorbed photon contributes to solar cell photocurrent. Minority carrier lifetimes in p-type CdTe are long, which results in high quantum efficiencies (number of electrons created per number of photons absorbed at a particular wavelength) of ~90% between 860 nm and 510 nm. Most photons absorbed in the CdTe film contribute to the solar cell photocurrent.

[0182] Solar light at wavelengths shorter than 510 nm is absorbed in the n-type CdS film and creates an electron-hole pair. Minority carriers in n-type CdS, holes, have short lifetimes. Most photogenerated holes recombine with electrons in the n-type CdS film before they can be swept across the junction to the p-type CdTe film. Recombined electron-hole pairs do not contribute to the solar cell photocurrent. Creation of electron-hole pairs by absorption of solar radiation in the CdS film is detrimental to the overall efficiency of the solar cell. High-efficiency solar cells make the CdS film as thin as possible, about 50 nm, so that some fraction of solar radiation shorter than 510 nm can pass through the CdS film and be absorbed in the CdTe film where the photo-generated electron-hole pairs can be efficiently collected. A problem with this procedure is that, in some embodiments, thinning the n-type CdS film increases the series resistance of the cell, which also decreases the efficiency. Additionally, the CdS film must have some reasonable thickness, ~50 nm, to form a stable pn junction.

[0183] The deposition methods according to the present invention are used to enhance the performance of heterojunction solar cells by creating higher quality semiconductor films **840**, **860**. In some embodiments, semiconductor films **840**, **860** have structures that provide sufficiently long minority-carrier lifetimes to allow the minority carriers to be swept across the junction and contribute to the solar cell photocurrent. In some embodiments, higher quality films **840**, **860** are produced by providing energy focused at the surface where a film is being formed. In some embodiments, the energy is supplied simultaneously with the material to be deposited on a substrate. In some embodiments, higher quality films are created by depositing the primary material, for example, CdS in the film **840**, using a physical vapor deposition technique while impinging energized particles from a second source on the film surface during the deposition. In some embodiments, the second source includes an

ion source. In some embodiments, the ion source provides a beam of ions. In some embodiments, the beam of ions includes argon or xenon. In some embodiments, the beam of ions includes sulfur for depositing sulfide materials. In some embodiments, the beam of ions includes oxygen for depositing oxide materials. The effect of supplying focused energy is to increase the extent of crystallinity of the material being deposited. Another effect of supplying focused energy is to decrease defects that provide sites for electron-hole recombination. A further enhancement of the solar cell efficiency is achieved by using the focused energy to control the quality of the physical interface between the first semiconductor film **840** and the second semiconductor film **860**.

[0184] In an embodiment, the first film **840** is fabricated by providing energy to the material being deposited so that the material has fewer defects. With fewer defects the minority carriers will have longer lifetimes in film **840** as the will be fewer recombination sites. In some embodiments, first film **840** includes an n-type CdS material. In some embodiments, the first film **840** is formed in a range of about 40 nanometers to about 100 nanometers. In some embodiments, the first film **840** has a thickness of about 50 nanometers. In some embodiments, the first film **840** is formed in a range of about 40 nanometers to about 100 nanometers.

[0185] In some embodiments, the second film **860** includes two regions **862**, **863**. Region **863** is a high-quality region formed according to the teachings of the present invention. In some embodiments, region **862** is grown in a faster manner using conventional methods. In other embodiments, film **862** is merely a further growth of film **863** using the teachings of the present invention. High quality includes, among other things, fewer defects, larger crystal size, or certain structures being formed. Specifically, energy is supplied to the material of region **863** as the material is formed on the first film **840**. The energy is supplied according to the teachings herein, for example, by an ion-assist beam. In some embodiments, the energy is supplied by energized particles. In some embodiments, the energy is supplied by energized ions. In some embodiments, the energy is supplied by light or heat, e.g., a brief laser sweep of the surface. Due to the application of energy while the region **863** is being formed, a post-deposition high-temperature anneal is not required.

[0186] In some embodiments, the high quality region **863** has fewer defects than p-type regions of other photovoltaics. In some embodiments, region **863** has a thickness of at least about 50 nanometers. In some embodiments, region **863** has a thickness in a range of about 50 nanometers to about 100 nanometers.

[0187] In some embodiments, region **862** is larger than region **863**. In some embodiments, region **862** has a thickness of greater than 500 nanometers. In some embodiments, region **862** has a thickness in a range of 1 micron to 5 microns. In some embodiments, region **862** has a thickness of greater than 3 microns. In addition, region **862** is a highly doped p-type material.

[0188] In some embodiments, a chamber in which the films **840**, **860** are being deposited is held at a temperature of less than 650 degrees Celsius. In some embodiments, the temperature of the chamber is less than about 300 degrees Celsius. In some embodiments, the temperature is between